## NSN 5961-01-225-0627

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View Online at https://aerobasegroup.com/nsn/5961-01-225-0627 **Inclosure Material:** Metal and glass **Overall Length:** 1.296 inches **End Application:** 1430-01-087-6337 information and coordination central, guided missle system **Mounting Facility Quantity:** 1 **Internal Configuration:** Junction contact **Mounting Method:** Threaded stud **Features Provided:** Burn in **Overall Width Across Flats:** Between 0.423 inches and 0.438 inches **Thread Size:** 0.190 inches **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 80.0 collector to emitter voltage/static/base open and 100.0 collector to base voltage/static/emitter open and 6.0 emitter to base voltage, static, collector open **Current Rating Per Characteristic:** 2.00 amperes source cutoff current and 1.00 amperes source cutoff current **Power Rating Per Characteristic:** 2.0 watts small-signal input power, common-collector absolute **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius junction **Special Features:** Junction pattern arrangement: pnp **Test Data Document:** 18876-11438979 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing) **Thread Series Designator:** Unf **Terminal Type And Quantity:** 3 tab, solder lug Shelf Life: N/a

No

**Unit Of Measure:** 

**Demilitarization:** 

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